



Correction: Analysis of contributions of electron-phonon relaxation and recombination processes to silicon heating by femtosecond laser pulse

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In the original publication of the article, Table 1 was incorrectly published. The correct table is given below:

The original article has been corrected.

Table 1 Quantitative parameters calculated using different models of the Auger recombination rate

	Maximum temperature (K)	Residual temperature (K)	Time to reach the maximum temperature (ps)	Relative contribution of Auger recombination to the maximum temperature (%)	Relative contribution of all types of recombination processes to the residual temperature (%)
$R_{Au}^{(1)}$	1398	353.6	21	29	46
$R_{Au}^{(2)}$	1430	353.4	13	31	46
$R_{Au}^{(3)}$	1412	353.7	24	30	46

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